	Type	Hits	Search Text	DBs
1	BRS	2	lee-yue-shiun.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	BRS	10	chen-cheng-hsiung.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	228	(nmos with transistor) and (poly adj gate) and (switch and simulation or simulate or equivalent)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	BRS	15	(nmos with transistor) and (poly adj gate) and (switch and simulation or simulate or equivalent) and induct$4 and resist$4 and capacit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	BRS	25	mos and transistor and (poly adj gate) and (switch and simulation or simulate or equivalent) and induct$4 and resist$4 and capacit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	BRS	47	(mos with transistor) and (switch with (simulat$3)) and induct$4 and resist$4 and capacit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	BRS	0	(nmos with transistor) and (poly adj gate) and switch and ((simulation or simulate) same (equivalent with circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	BRS	0	(mos with transistor) and (poly adj gate) and switch and ((simulation or simulate) same (equivalent with circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	BRS	0	(mos with transistor) and (poly adj gate) and (switch same (simulation or simulate) same (equivalent with circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	BRS	9	(mos with transistor) and (switch same (simulation or simulate) same (equivalent with circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
11	BRS	67	((mos with transistor) same switch same (simulation or simulate or equivalent)) and induct$4 and resist$4 and capacit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	BRS	11	((mos with transistor) same (equivalent with circuit) same switch) and intrinsic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	BRS	201	(mos with transistor) same (equivalent with circuit) same switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	BRS	23	(mos with transistor with switch) same intrinsic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
15	BRS	5	(mos with transistor with modeling) same (equivalent with circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
16	BRS	168	(mos same model$3 same substrate) and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
17	BRS	59	(mos same model$3 same switch) and transistor and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
18	BRS	1	(mos same model$3 same switch same spice) and transistor and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
19	BRS	16	(mos with transistor with model$3) same (equivalent with circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
20	BRS	10	(mos same model$3 same spice) and transistor and substrate and switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
21	BRS	262	333/101.ccls.	USPAT
22	BRS	270	333/103.ccls.	USPAT
23	BRS	177	257/107.ccls.	USPAT
24	BRS	28	257/120.ccls.	USPAT
25	BRS	275	257/204.ccls.	USPAT

	Type	Hits	Search Text	DBs
26	BRS	614	703/14.ccls.	USPAT